Leakage Compensated Charge Method for Determining Static C-V Characteristics of Ultra-Thin MOS Capacitors

Characterization of Ultra-Thin Oxides Using Electrical C-V and I-V Measurements

Threshold Voltage ($V_{T}$) Control of Sub-0.25 [μm] Processes Using Mercury Gate MOS Capacitors

Advances in Surface Photovoltage Technique for Monitoring of the IC Processes

Non-Contact Monitoring of Electrical Characteristics of Silicon Surface and Near-Surface Region

Contactless Transient Spectroscopy for the Measurement of Localized States in Semiconductors

Tunneling Spectroscopy of the Silicon Metal-Oxide-Semiconductor System

Characterization of Ultra-Shallow Junctions with Tapered Groove Profilometry and Other Techniques

A New Low Thermal Budget Approach to Interface Nitridation for Ultra-Thin Silicon Dioxide Gate Dielectrics by Combined Plasma-Assisted and Rapid Thermal Processing

Development of a Metrology Method for Composition and Thickness of Barium Strontium Titanate Thin Films

Physical and Chemical Characterization of Barium Strontium Titanate Thin Films

Suppression of Boron Penetration for P[superscript +] Polysilicon Gate Electrodes by Ultra-Thin RPECVD Nitride Films in Composite Oxide-Nitride Dielectrics

Luminescence Measurements of Sub-Oxide Band-Tail and Si Dangling Bond States at Ultrathin Si-SiO$_2$[subscript 2] Interfaces

Optical Studies of Phosphorus-Doped Poly-Si Films

Calibration Wafer for Temperature Measurements in RTP Tools

Rapid Non-Invasive Temperature Measurement of Complex Si Structures Using In-Situ Spectroscopic Ellipsometry

Fabrication of SiGe and SiGeC Epitaxial Layers by Ion Implantation and Excimer Laser Annealing

Application of Electrical Step Resistance Measurement Technique for ULSI/VLSI Process Characterization

In-Situ Surface and Interface Characterization by Optical Second Harmonic Generation (SHG) of Silicon Dioxide Fabrication with High Purity Ozone

Analysis of Reflectometry and Ellipsometry Data from Patterned Structures

In Situ Layer Characterization by Spectroscopic Ellipsometry at High Temperatures

Instrumental and Computational Advances for Real-Time Process Control Using Spectroscopic Ellipsometry

Evaluation of an Automated Spectroscopic Ellipsometer for In-Line Process Control

Metrology Standards with Ellipsometers

Evaluation of Surface Depletion Effects in Single-Crystal Test Structures for Reference Materials Applications

In-Situ Real-Time Mass Spectroscopic Sensing and Mass Balance Modeling of Selective Area Silicon PECVD

Optical Densitometry Applications for Ion Implantation

Interconnect